

Progress of IBC Si solar cells

(ACAP PP1.2a)

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PVLighthouse: Keith McIntosh

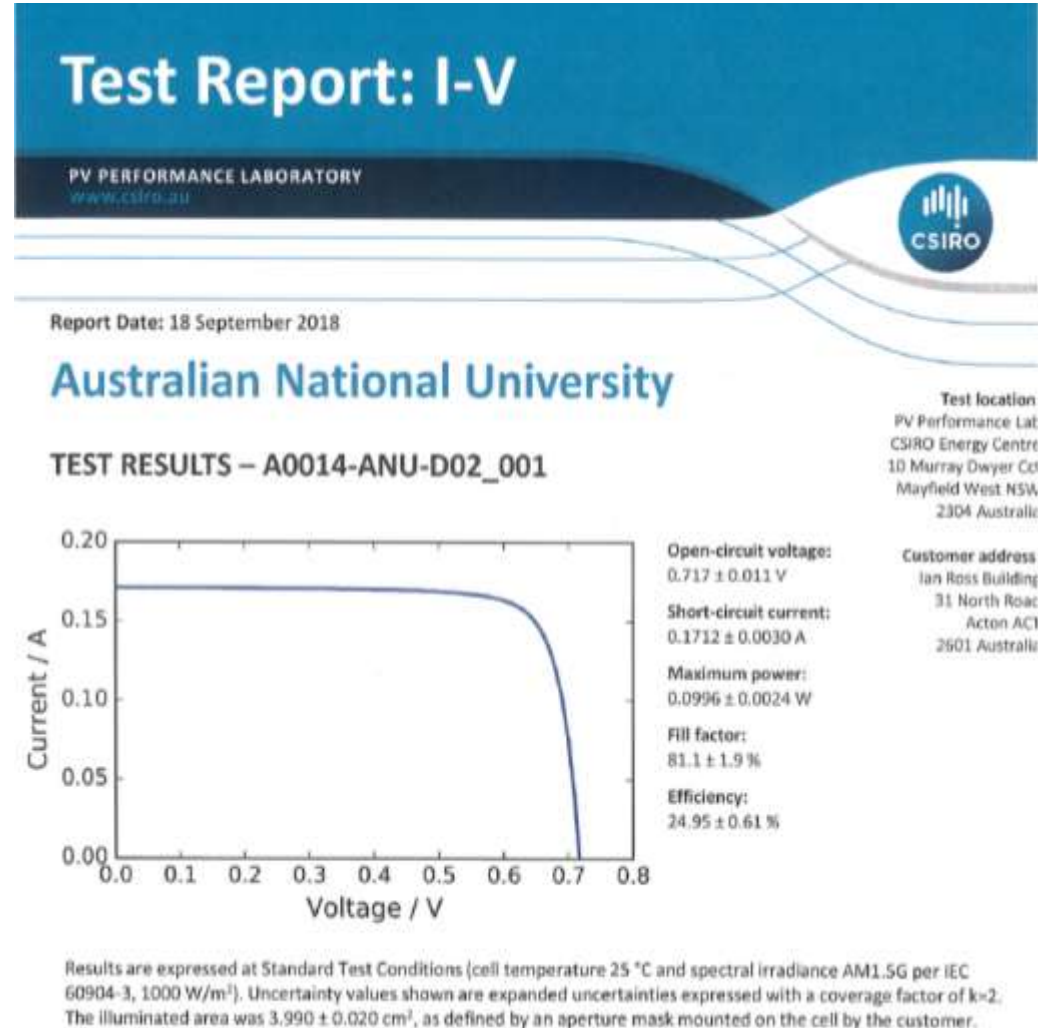
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In 2018, ANU received certification for a **24.95 ± 0.61%** single-junction Si solar cell.

- V_{OC} 717 mV
- J_{SC} 42.9 mA cm⁻²,
- FF 81.1

Key features of the cell:

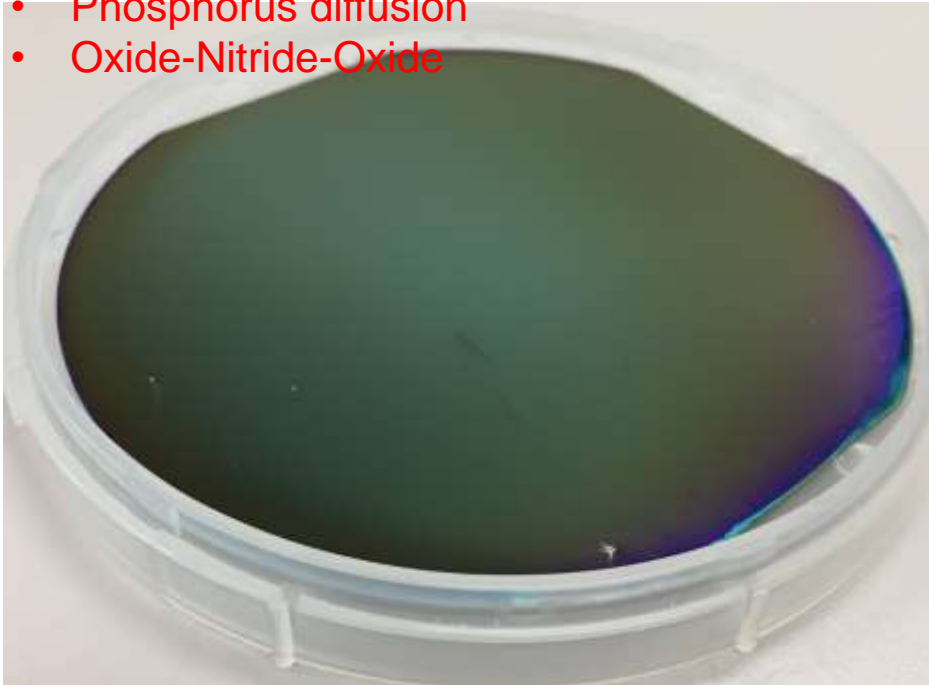
- Oxide-Nitride-Oxide passivation
- High bulk lifetime >50ms
- Excellent light trapping



ANU 25% IBC Solar Cell

Front surface:

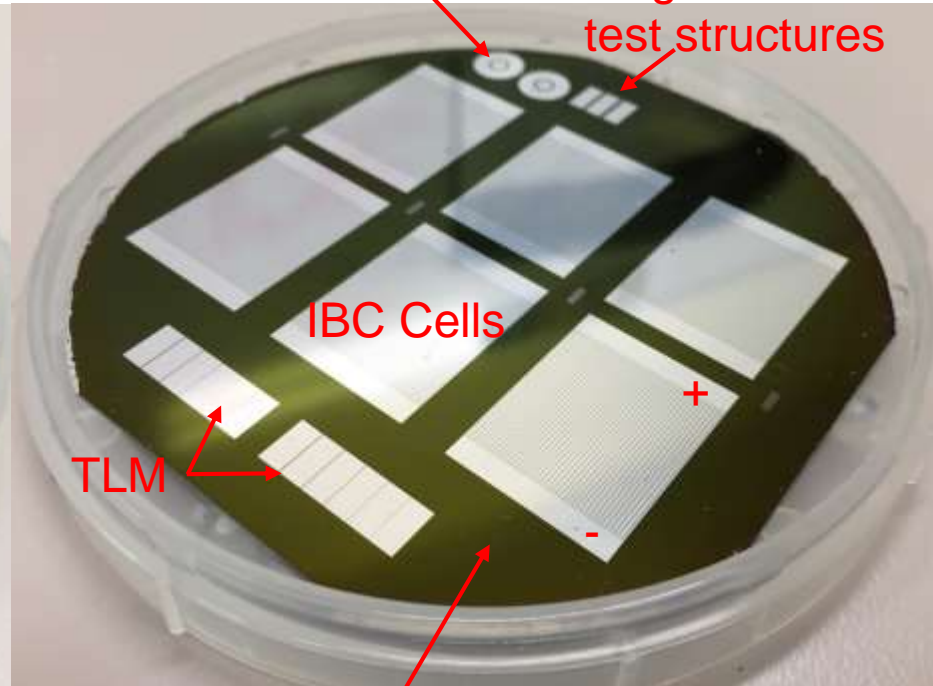
- Textured
- Phosphorus diffusion
- Oxide-Nitride-Oxide



Dielectric

test structures

Finger resistance
test structures

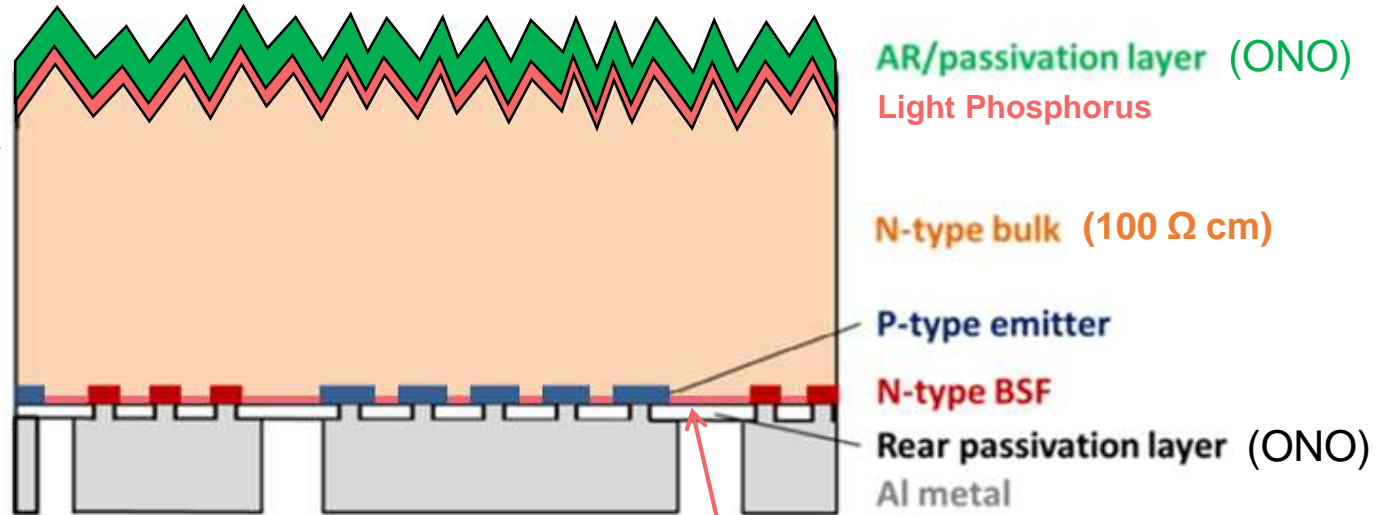


Rear surface:

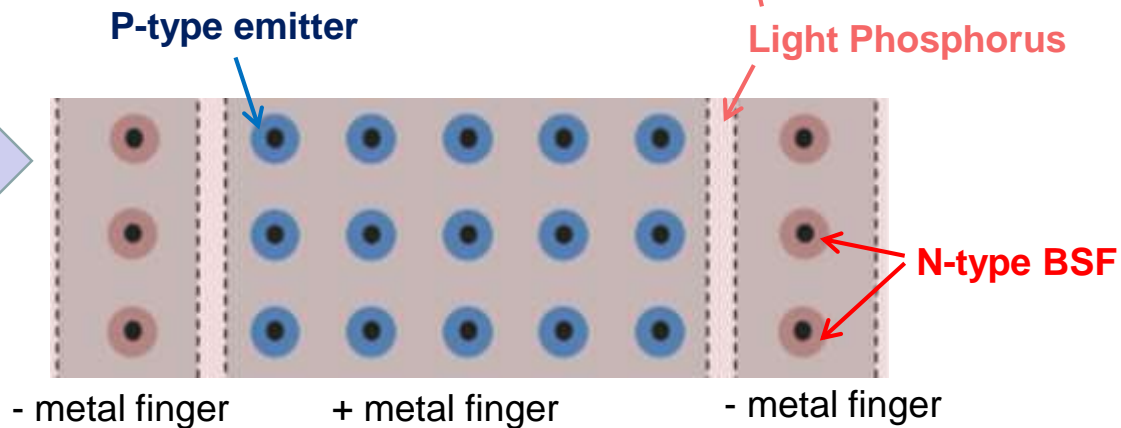
- Non-textured
- Phosphorus diffusion
- Oxide-Nitride-Oxide

ANU 25% IBC Solar Cell

Cross section

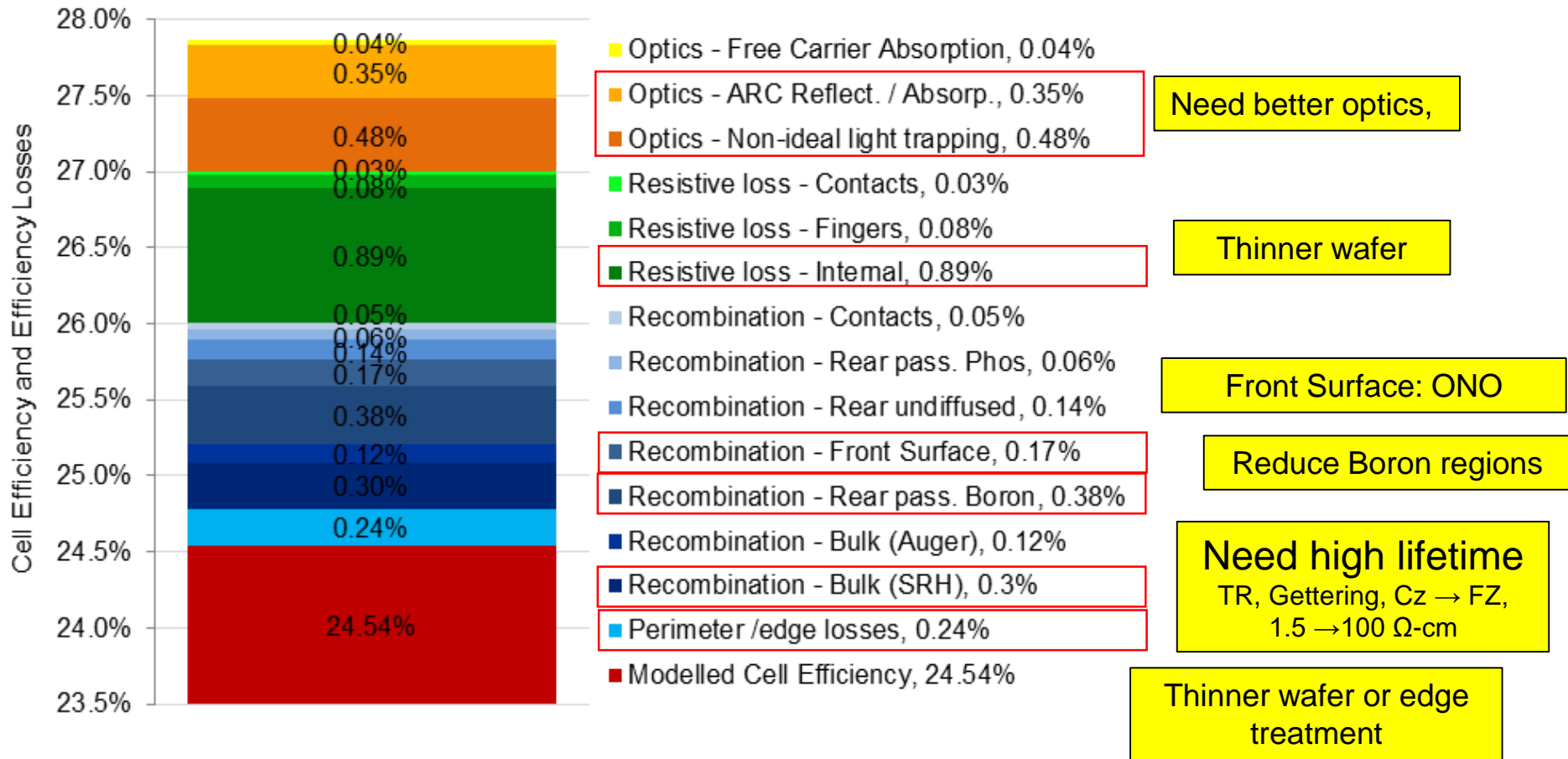


Bottom-up View



Key design improvements

Loss analysis of (2014) 24.4% IBC cell:

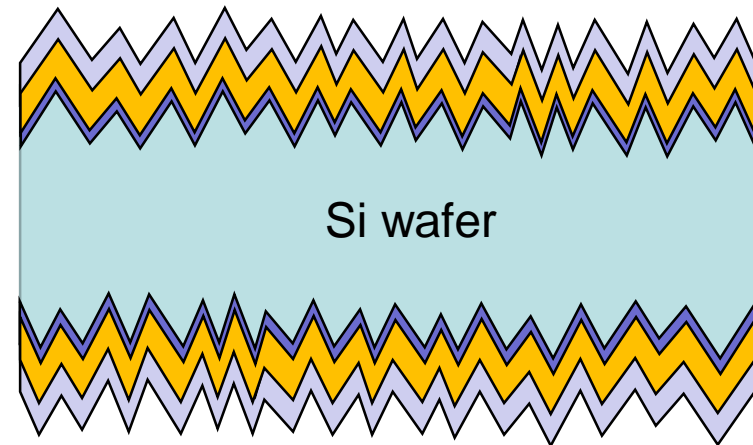
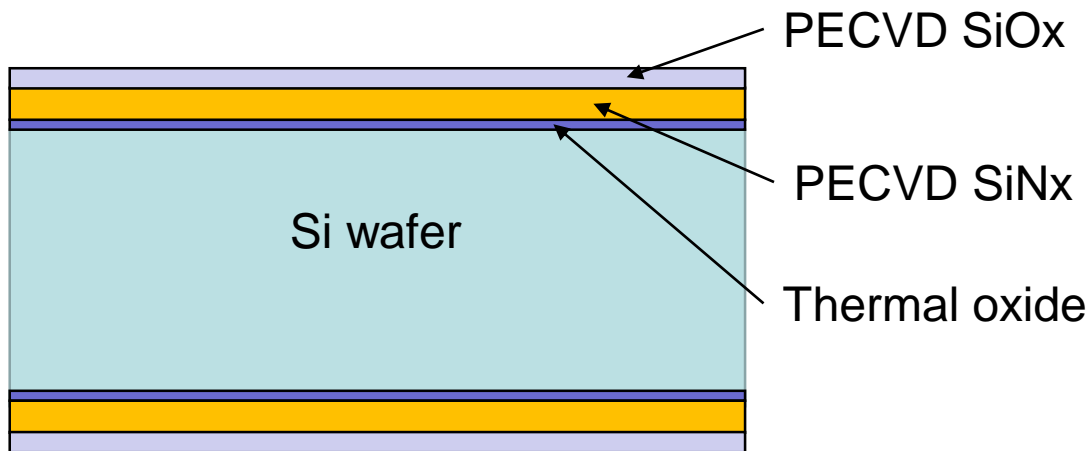


Franklin E., Fong K.C., et al, *Progress in Photovoltaics: Research and Applications*, 2014

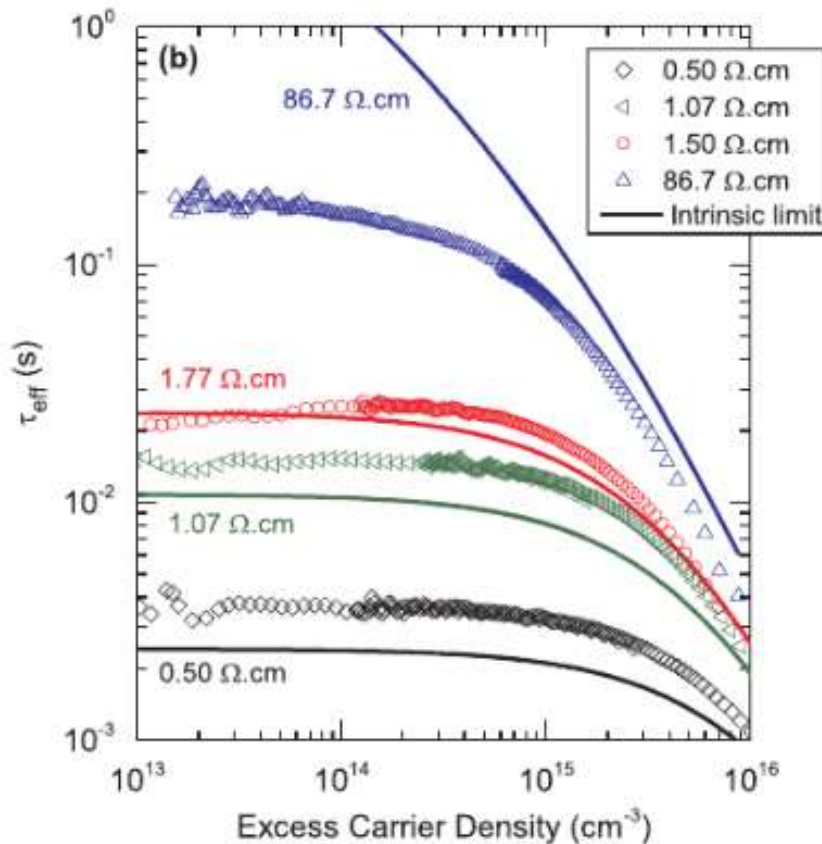
Origin:

The idea of ONO passivation is derived from SONOS memory cells, which has properties of being chargeable with good charge retention capacity.

It turns out, that an ONO performs excellently as a passivation layer, and surface charges can be tuned from +ve to -ve.



O-N-O on undiffused Si

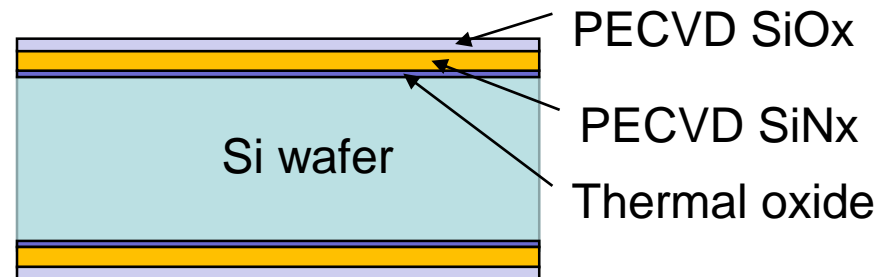


Planar:

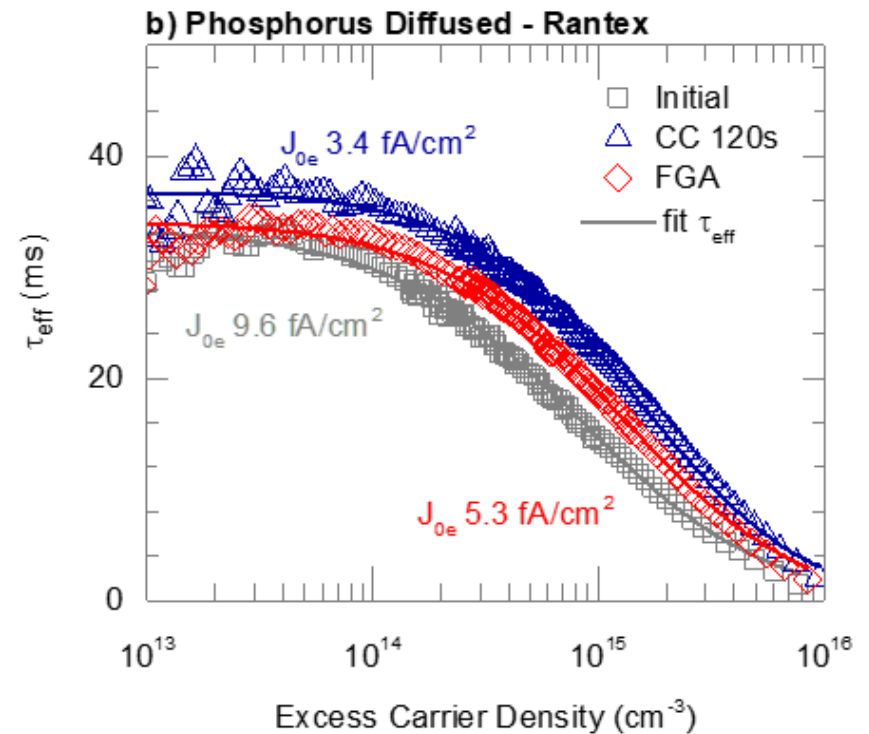
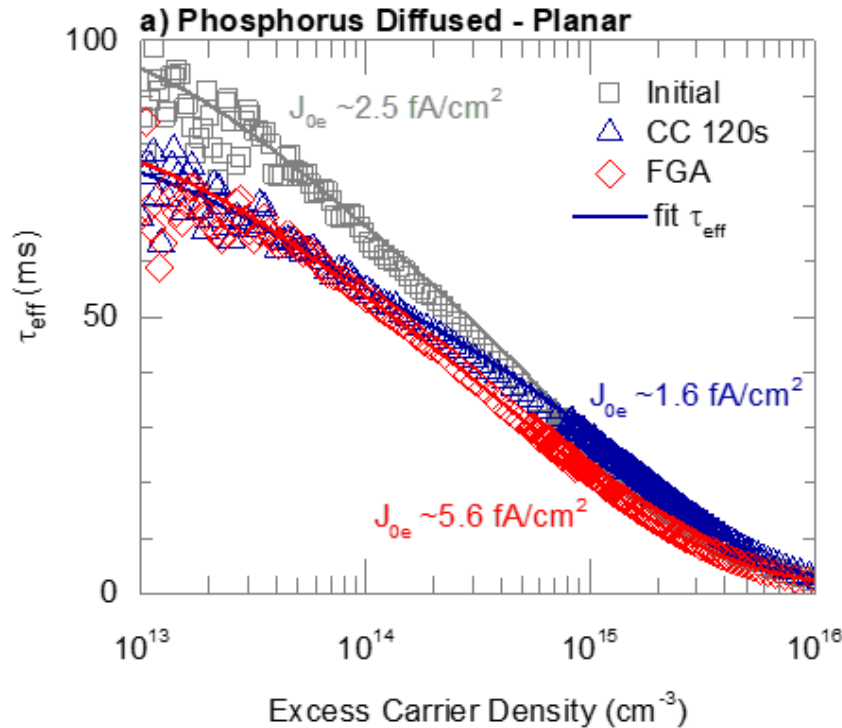
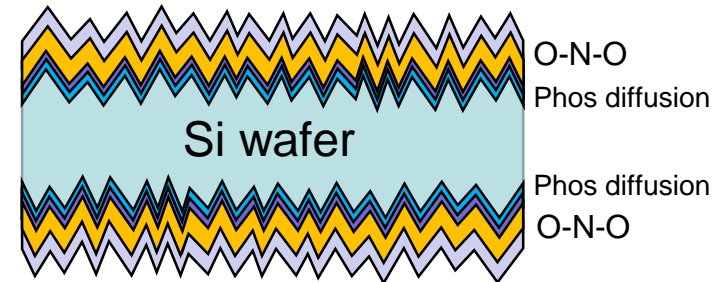
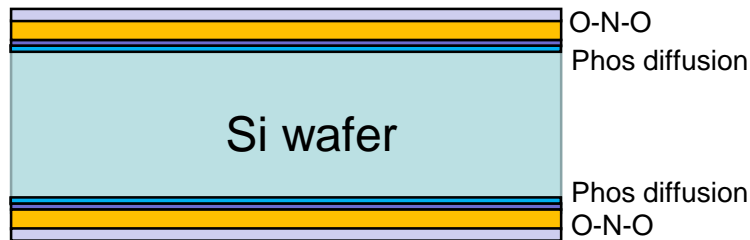
- $< 0 \text{ fAcm}^{-2}$, exceeding (Richter) Auger lifetime limits.

Random Textured:

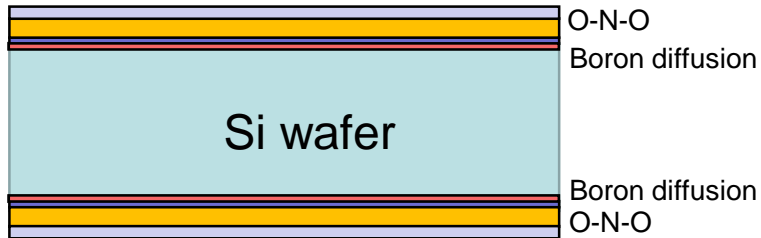
- $\sim 1\text{-}5 \text{ fAcm}^{-2}$



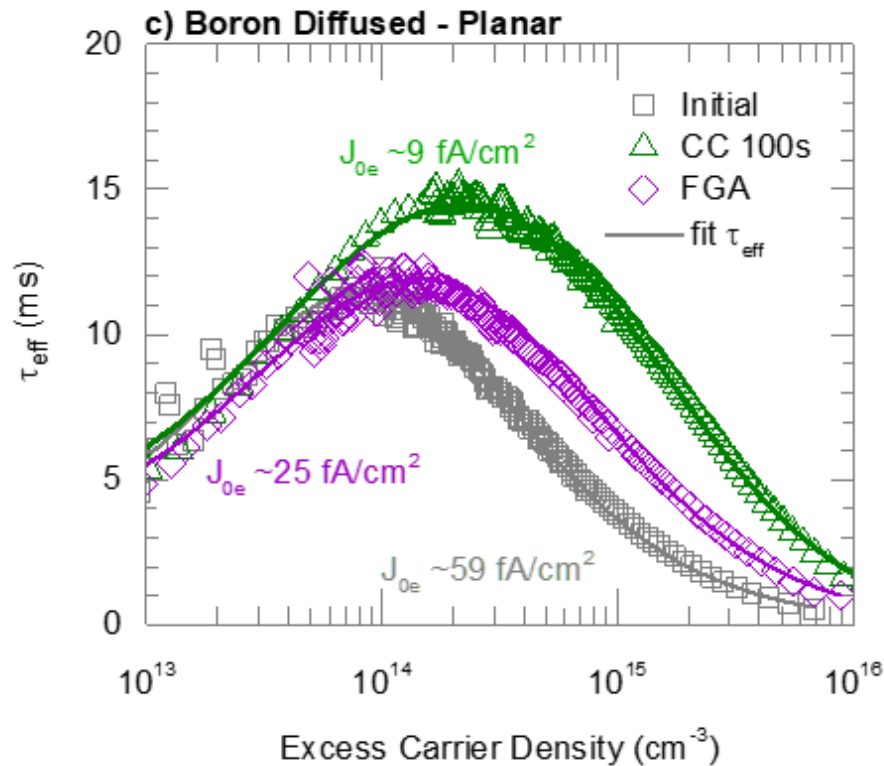
Phos diffused ONO



Boron diffused- ONO

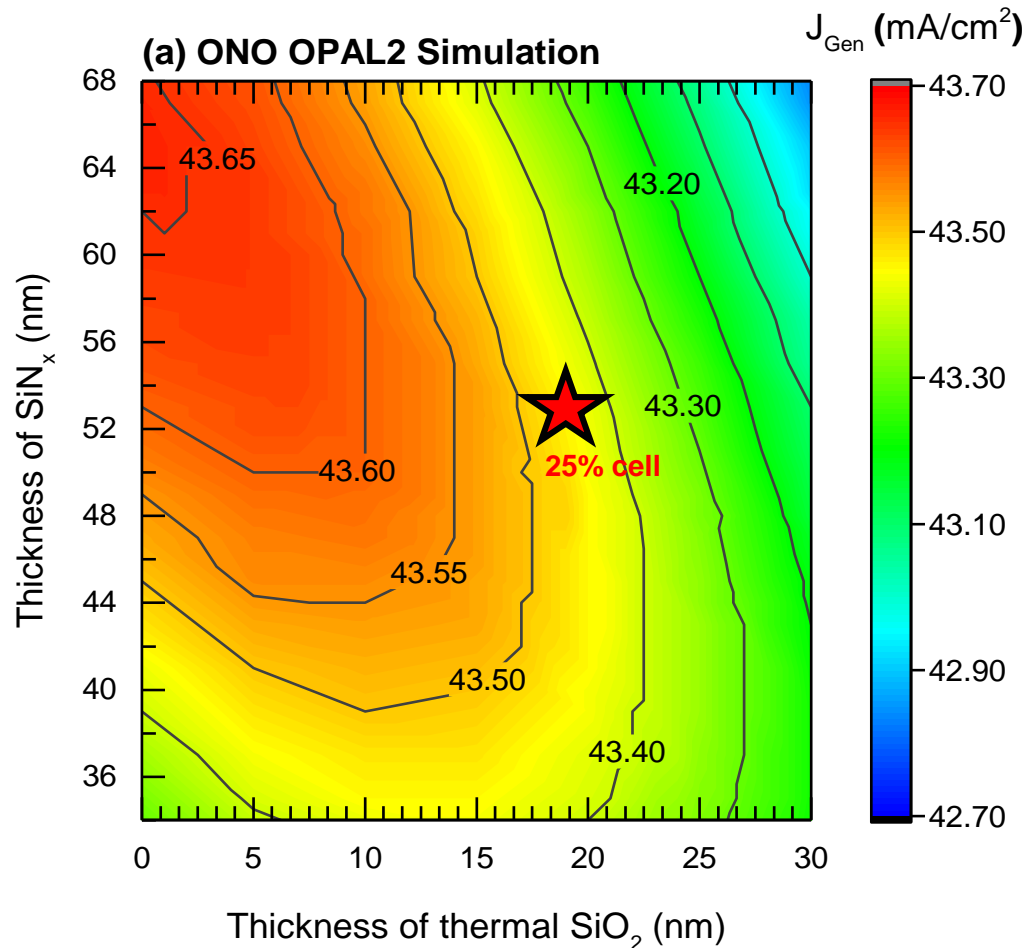


- Uncharged 25 fAcm^{-2}
- Negatively charged J_0 at 9 fAcm^{-2}

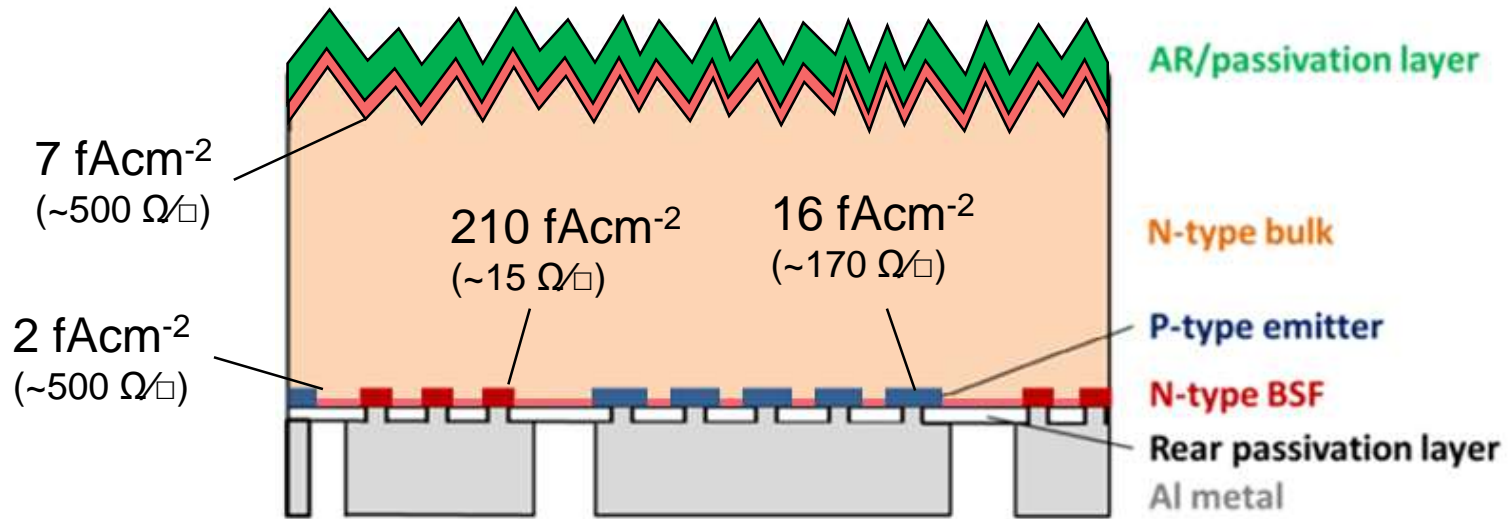


Optimal Optics is achieved when SiO₂ is thinnest.

- Trade-off between optics & passivation



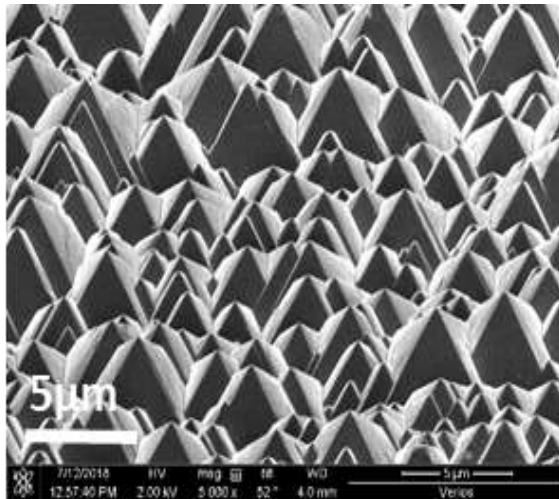
Application of ONO to IBC cells



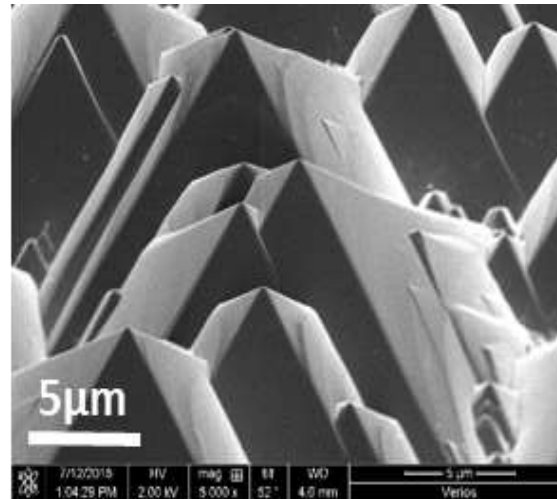
Area Weighted J_0 indicates the surfaces and contacts contribute approximately 16 fAcm^{-2} to the entire cell.

Improvement to Texturing

- ANU adopted the use of monoTEX additive for the formation of random pyramid structures.
 - **Physical** : Uniform, repeatable, smaller pyramids (~3 μ m), consumes less silicon (~10 μ m)
 - **Electrical** : Slightly higher bulk lifetimes achieved in controlled test versus TMAH-IPA texturing.



TMAH + MonoTEX
(presented improvement)



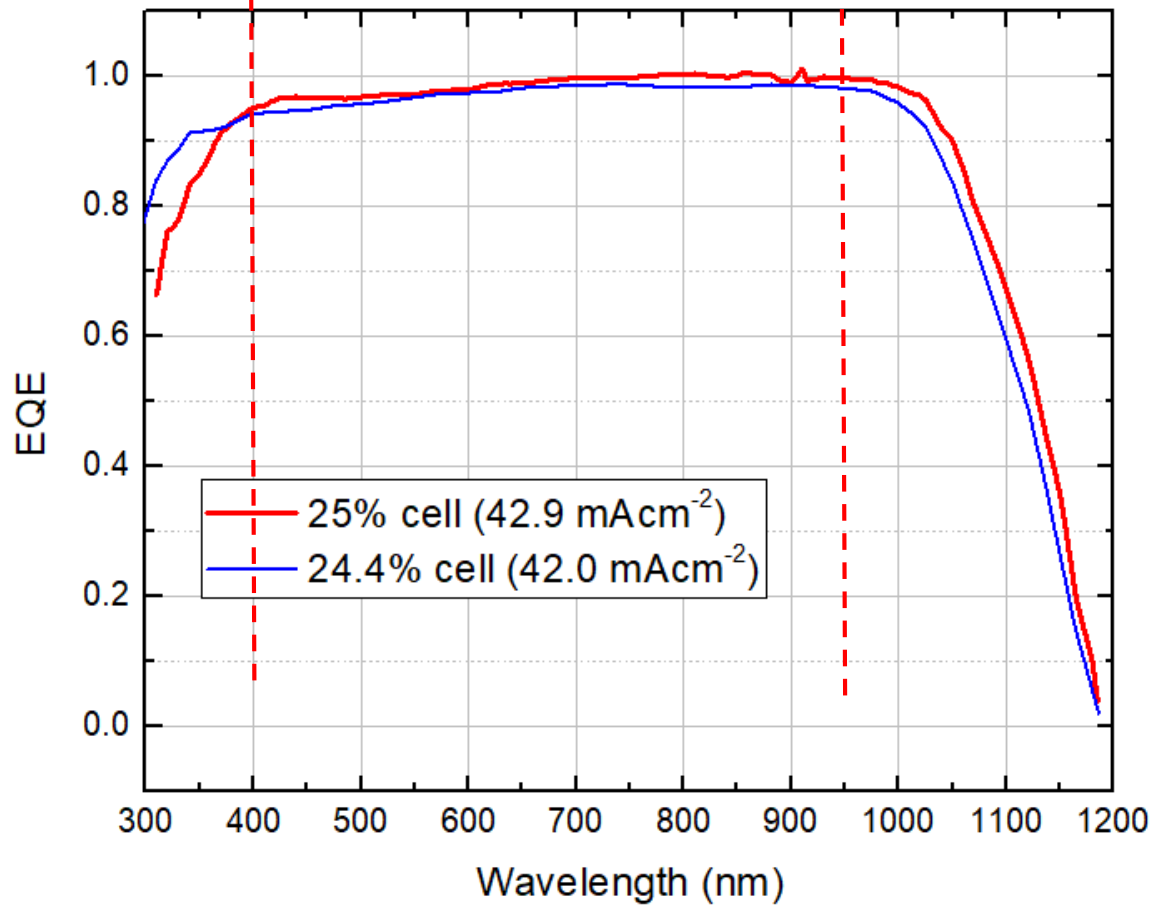
TMAH + IPA

Quantum Efficiency

300-400 nm
-0.04 mA cm⁻²

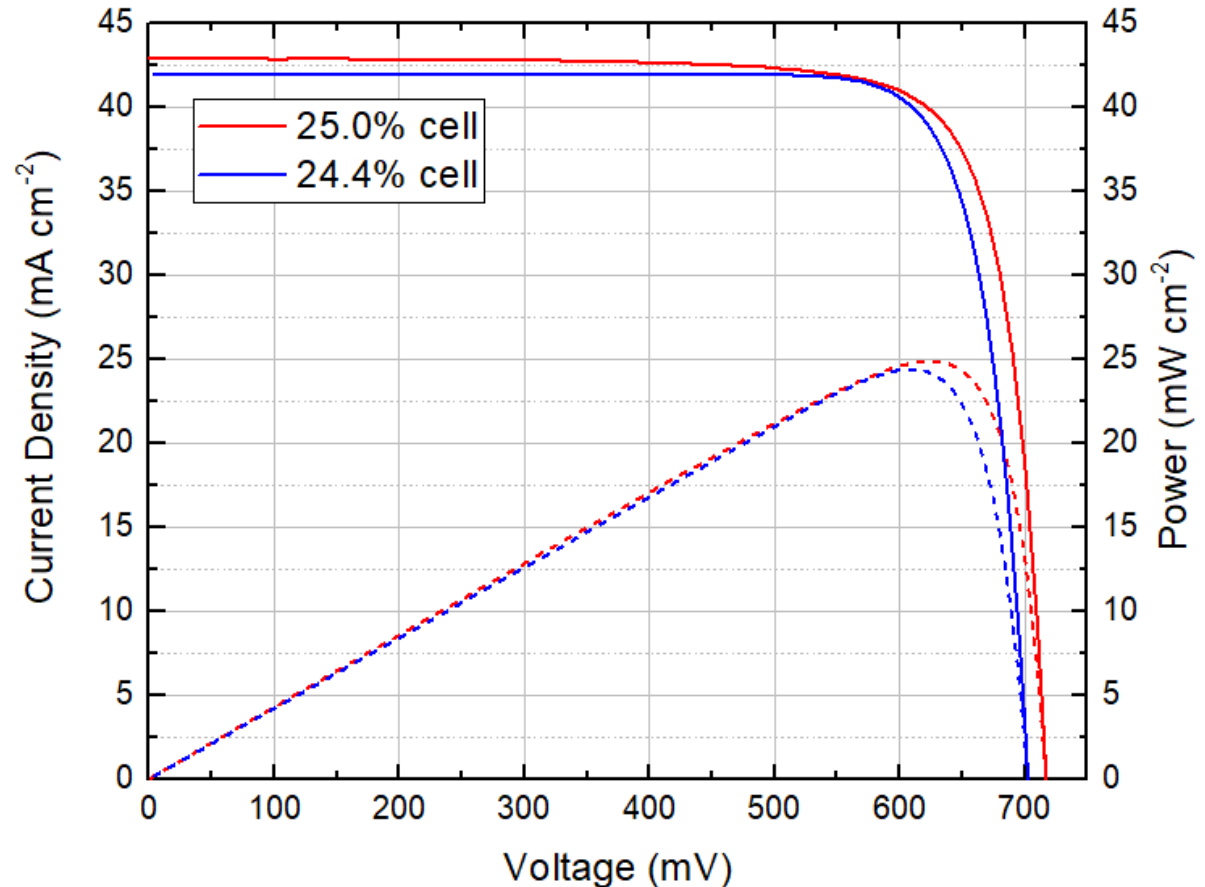
400-950 nm
+0.4 mA cm⁻²

950-1200 nm
+0.5 mA cm⁻²

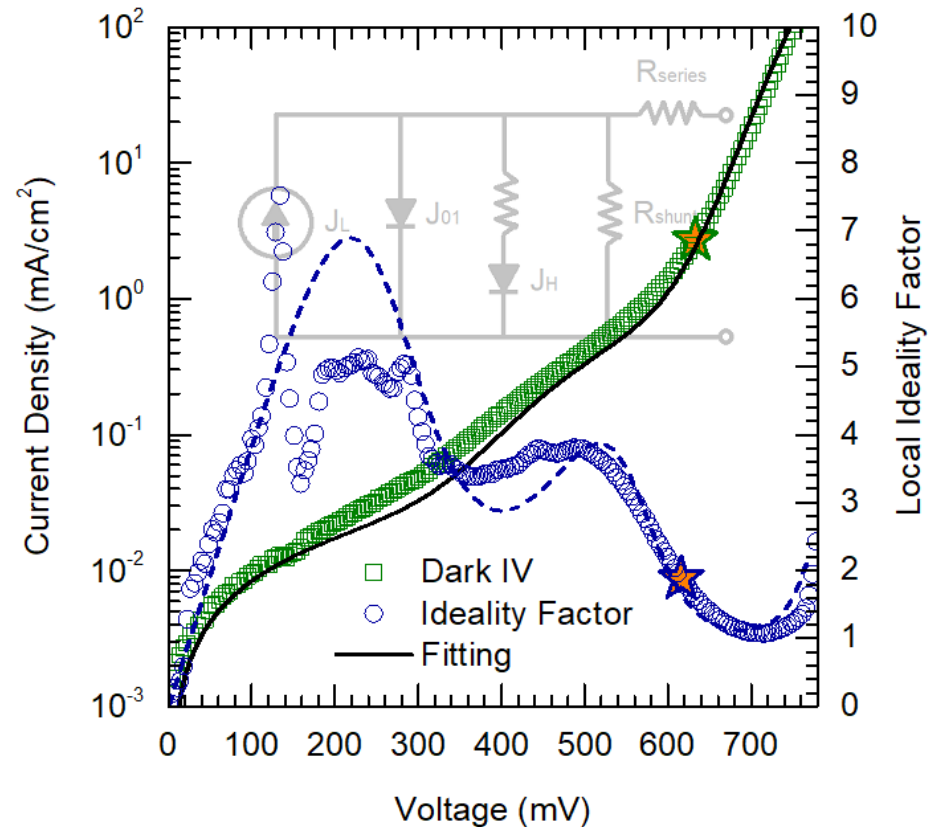


IV measurements

- High V_{OC} of 717 mV..
- Bulk lifetime >50ms before metallisation.
- High J_{SC} of 42.9mAcm^{-2} .
- But weak knee, low FF of 81.1.



- Low FF, identifying source of non-ideality
- Application of passivated contacts in combination with ONO



ANU IBC Cell progression

2013: 24.4% (independently confirmed)

- 703mV, 42.0 mAcm⁻², FF 82.7%
- 1.5 Ohm-cm n-type
- PECVD SiN/SiO front, LPCVD SiO/SiN rear.



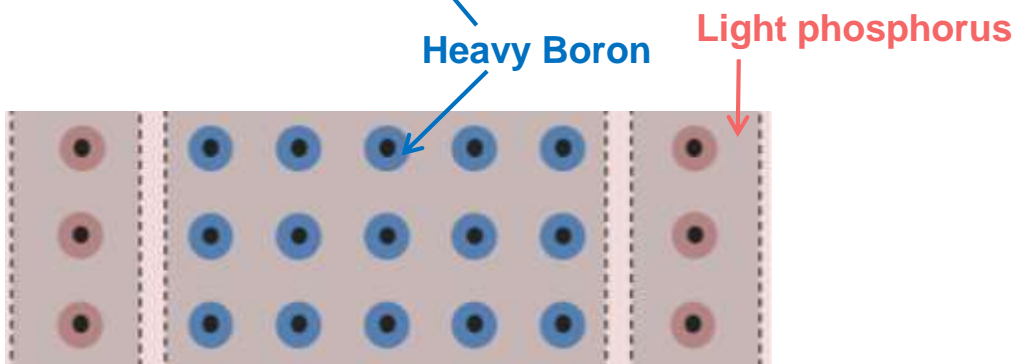
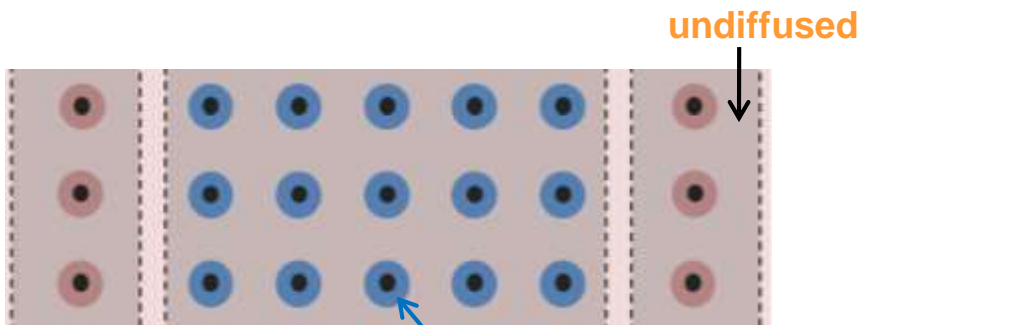
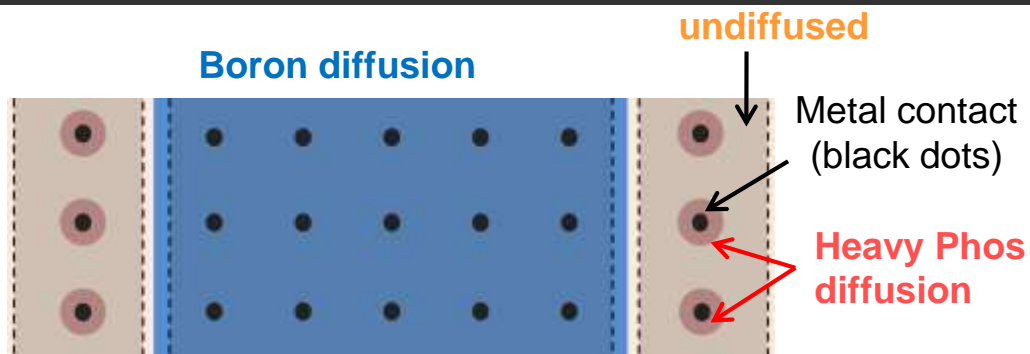
2016: 24.7% (in-house)

- 714mV, 42.0 mAcm⁻², FF 82.3%
- High resistivity (100 Ohm-cm)
- ONO passivation
- Phosphorus gettering



2018: 25.0% (independently confirmed)

- 717mV, 42.9 mAcm⁻², FF 81.1%
- Phos + BRL gettering
- Improved texturing (MonoTex)



- metal finger (shaded) + metal finger (shaded) - metal finger (shaded)

- 25% efficient IBC cells fabricated at ANU.
- Key features: ONO, TMA-MonoTEX, Bulk lifetime (TR, BRL & Phos gettering.)
- Publications:
 - T. K. Choon, K.C. Fong, *et al.*, *SOLMAT*, 2018.
 - W. S. Liang, K.C. Fong, *et al.*, *ASPVC*, 2018.
 - E. Franklin, K.C. Fong, *et al.*, *PIPV*, 2016.
 - K.C Fong, *et,al*, *JPV*, 2016.
 - K.C Fong, *et,al*, *JPV*, 2015.
 - A.Fell, K.C. Fong, *JPV*, 2014
 - K.R. McIntosh, *PVSC* 2014, ... many more...
- Open to collaboration.